

2N6284 (NPN); 2N6286, 2N6287 (PNP)

Preferred Device

Darlington Complementary Silicon Power Transistors

These packages are designed for general-purpose amplifier and low-frequency switching applications.

Features

- High DC Current Gain @ $I_C = 10 \text{ Adc}$ –
 $h_{FE} = 2400 \text{ (Typ)} - 2N6284$
 $= 4000 \text{ (Typ)} - 2N6287$
- Collector–Emitter Sustaining Voltage –
 $V_{CEO(sus)} = 100 \text{ Vdc (Min)}$
- Monolithic Construction with Built–In Base–Emitter Shunt Resistors
- Pb–Free Packages are Available*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	80 100	Vdc
Collector–Base Voltage	V_{CB}	80 100	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous Peak	I_C	20 40	Adc
Base Current	I_B	0.5	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	160 0.915	W W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	–65 to +200	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	1.09	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

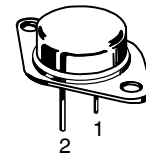
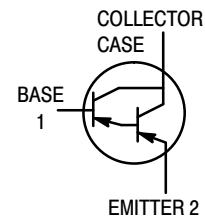
1. Indicates JEDEC Registered Data.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

20 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 100 VOLTS, 160 WATTS



TO–204AA (TO–3)
CASE 1–07
STYLE 1

MARKING DIAGRAM



2N628x = Device Code
x = 4, 6 or 7
G = Pb–Free Package
A = Location Code
YY = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
2N6284	TO–3	100 Units/Tray
2N6284G	TO–3 (Pb–Free)	100 Units/Tray
2N6286	TO–3	100 Units/Tray
2N6286G	TO–3 (Pb–Free)	100 Units/Tray
2N6287	TO–3	100 Units/Tray
2N6287G	TO–3 (Pb–Free)	100 Units/Tray

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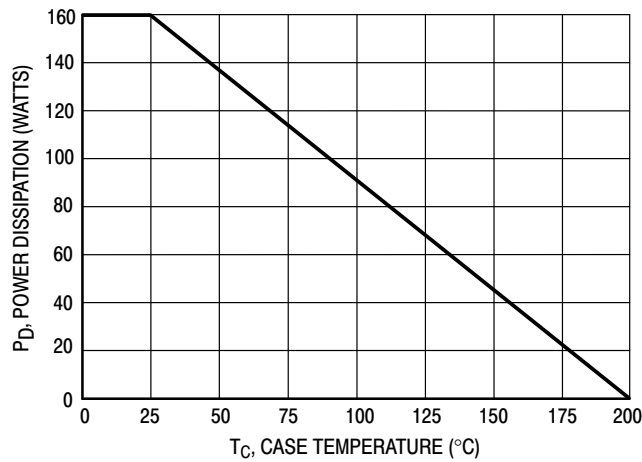


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ($I_C = 0.1 \text{ A dc}$, $I_B = 0$)	$V_{CEO(sus)}$	80	–	Vdc
		100	–	
				2N6286 2N6284, 2N6287
Collector Cutoff Current ($V_{CE} = 40 \text{ Vdc}$, $I_B = 0$) ($V_{CE} = 50 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	–	1.0	mAdc
		–	1.0	
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CB}$, $V_{BE(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = \text{Rated } V_{CB}$, $V_{BE(off)} = 1.5 \text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	–	0.5	mAdc
		–	5.0	
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	2.0	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$) ($I_C = 20 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$)	h_{FE}	750	18,000	–
		100	–	
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ A dc}$, $I_B = 40 \text{ mAdc}$) ($I_C = 20 \text{ A dc}$, $I_B = 200 \text{ mAdc}$)	$V_{CE(sat)}$	–	2.0	Vdc
		–	3.0	
Base–Emitter On Voltage ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$)	$V_{BE(on)}$	–	2.8	Vdc
Base–Emitter Saturation Voltage ($I_C = 20 \text{ A dc}$, $I_B = 200 \text{ mAdc}$)	$V_{BE(sat)}$	–	4.0	Vdc
DYNAMIC CHARACTERISTICS				
Magnitude of Common Emitter Small–Signal Short–Circuit Forward Current Transfer Ratio ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	$ h_{fe} $	4.0	–	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 0.1 \text{ MHz}$)	C_{ob}	–	400	pF
		–	600	
				2N6284 2N6286, 2N6287
Small–Signal Current Gain ($I_C = 10 \text{ A dc}$, $V_{CE} = 3.0 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	300	–	–

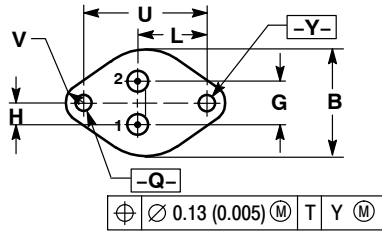
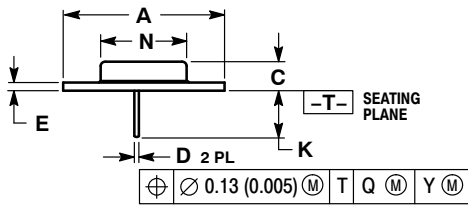
2. Indicates JEDEC Registered Data.

3. Pulse test: Pulse Width = 300 μs , Duty Cycle = 2%

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PACKAGE DIMENSIONS

TO-204 (TO-3)
CASE 1-07
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:

- PIN 1. BASE
2. EMITTER
CASE: COLLECTOR